



RISC Microprocessor Module

PRELIMINARY*

OVERVIEW

The WEDC 750/SSRAM module is targeted for high performance, space sensitive, low power systems and supports the following power management features: doze, nap, sleep and dynamic power management.

The WED3C750A8M-200BX multi-chip package consists of:

- 750 RISC processor
- Dedicated 1MB SSRAM L2 cache, configured as 128Kx72
- 21mmx25mm, 255 Ceramic Ball Grid Array (CBGA)
- Maximum Core frequency = 200MHz
- Maximum L2 Cache frequency = 100MHz
- Maximum 60x Bus frequency = 66MHz

The WED3C750A8M-200BX is offered in industrial (-40°C to +85°C) and military (-55°C to +125°C) temperature ranges and is well suited for embedded applications such as missiles, aerospace, flight computers, fire control systems and rugged critical systems.

* This data sheet describes a product under development, not fully characterized, and is subject to change without notice.

FIG. 1 Multi-Chip Package Diagram

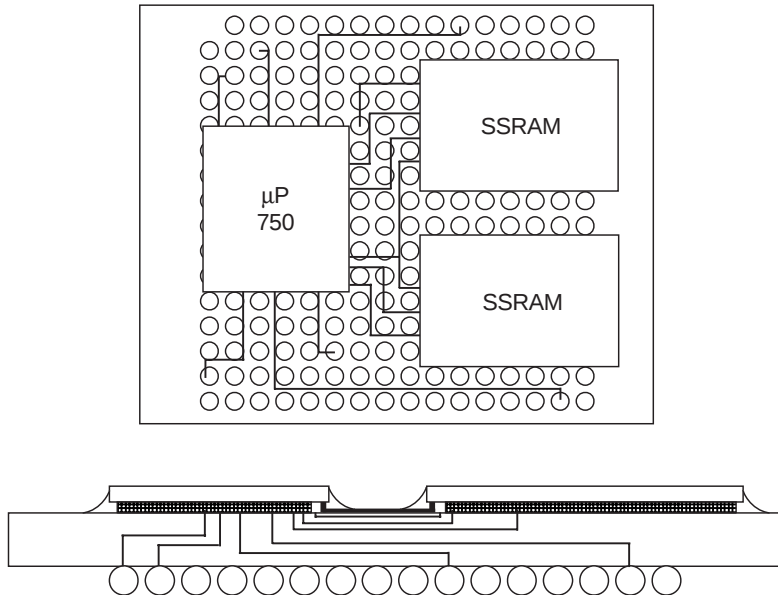




FIG. 2 Block Diagram

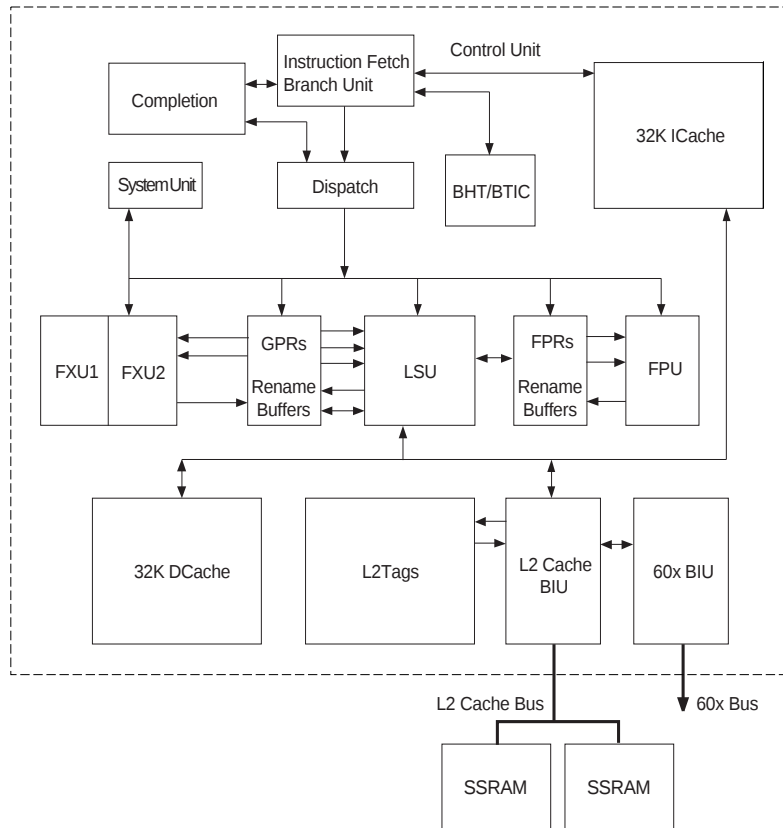




FIG. 3 Block Diagram, L2 Interconnect

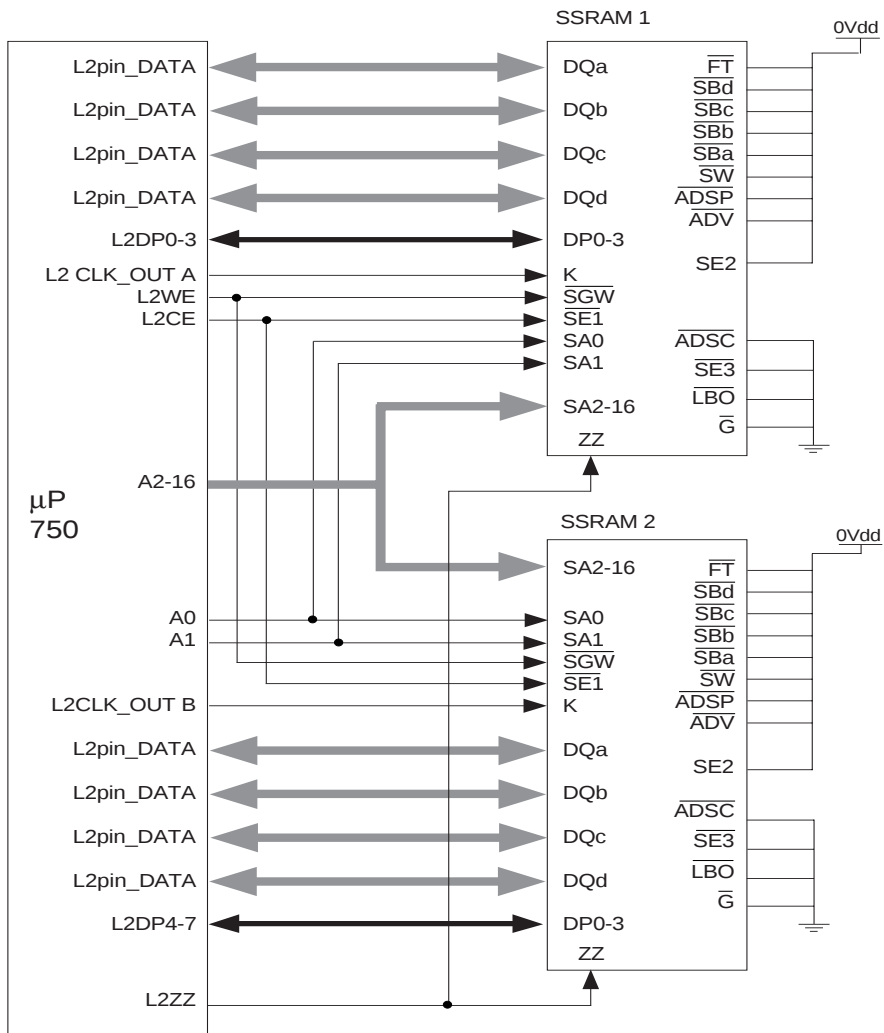
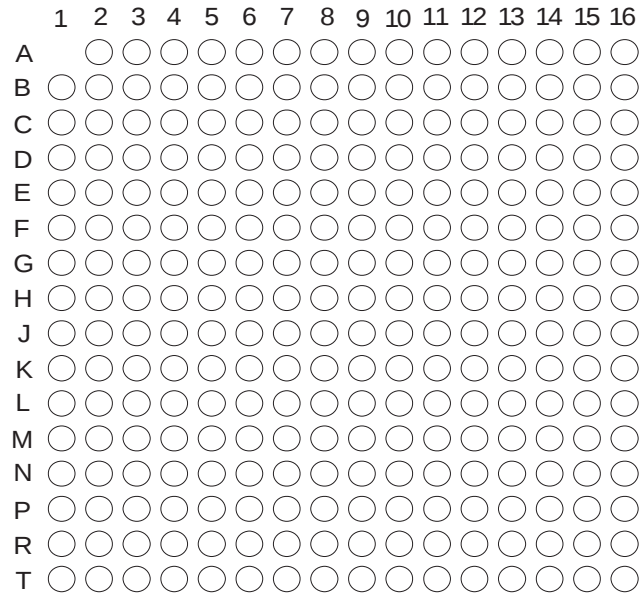


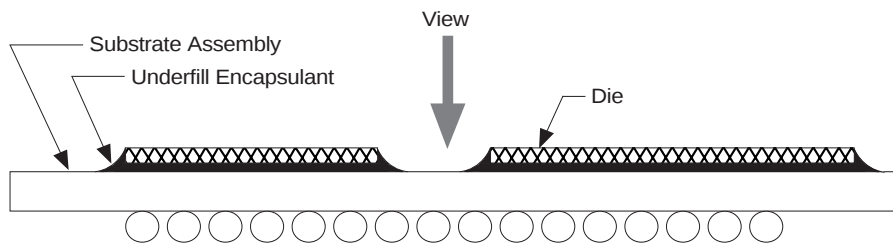


FIG. 4 Pin Assignments

Ball assignments of the 255 CBGA package as viewed from the top surface.



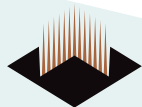
Side profile of the CBGA package to indicate the direction of the top surface view.





PACKAGE PINOUT LISTING

Signal Name	Pin Number	Active	I/O
A[0-31]	C16, E4, D13, F2, D14, G1, D15, E2, D16, D4, E13, G2, E15, H1, E16, H2, F13, J1, F14, J2, F15, H3, F16, F4, G13, K1, G15, K2, H16, M1, J15, P1	High	I/O
AACK	L2	Low	Input
ABB	K4	Low	I/O
AP[0-3]	C1, B4, B3, B2	High	I/O
ARTRY	J4	Low	I/O
AVDD	A10	—	—
BG	L1	Low	Input
BR	B6	Low	Output
CI	E1	Low	Output
CKSTP_IN	D8	Low	Input
CKSTP_OUT	A6	Low	Output
CLK_OUT	D7	—	Output
DBB	J14	Low	I/O
DBG	N1	Low	Input
DBDIS	H15	Low	Input
DBWO	G4	Low	Input
DH[0-31]	P14, T16, R15, T15, R13, R12, P11, N11, R11, T12, T11, R10, P9, N9, T10, R9, T9, P8, N8, R8, T8, N7, R7, T7, P6, N6, R6, T6, R5, N5, T5, T4	High	I/O
DL[0-31]	K13, K15, K16, L16, L15, L13, L14, M16, M15, M13, N16, N15, N13, N14, P16, P15, R16, R14, T14, N10, P13, N12, T13, P3, N3, N4, R3, T1, T2, P4, T3, R4	High	I/O
DP[0-7]	M2, L3, N2, L4, R1, P2, M4, R2	High	I/O
DRTRY	G16	Low	Input
GBL	F1	Low	I/O
GND	C5, C12, E3, E6, E8, E9, E11, E14, F5, F7, F10, F12, G6, G8, G9, G11, H5, H7, H10, H12, J5, J7, J10, J12, K6, K8, K9, K11, L5, L7, L10, L12, M3, M6, M8, M9, M11, M14, P5, P12	—	—
HRESET	A7	Low	Input
INT	B15	Low	Input
L1_TSTCLK (1)	D11	High	Input
L2_TSTCLK (1)	D12	High	Input
LSSD_MODE (1)	B10	Low	Input
MCP	C13	Low	Input
NC (No-connect)	B7, B8, C3, C6, C8, D5, D6, H4, J16, A4, A5, A2, A3, B1, B5	—	—
OVDD (2)	C7, E5, E7, E10, E12, G3, G5, G12, G14, K3, K5, K12, K14, M5, M7, M10, M12, P7, P10	—	—
PLL_CFG[0-3]	A8, B9, A9, D9	High	Input
QACK	D3	Low	Input
QREQ	J3	Low	Output
RSRV	D1	Low	Output
SMI	A16	Low	Input
SRESET	B14	Low	Input
SYSCLK	C9	—	Input
TA	H14	Low	Input
TBEN	C2	High	Input
TBST	A14	Low	I/O



PACKAGE PINOUT LISTING (continued)

Signal Name	Pin Number	Active	I/O
TCK	C11	High	Input
TDI	A11	High	Input
TDO	A12	High	Output
$\overline{\text{TEA}}$	H13	Low	Input
TLBISYNC	C4	Low	Input
TMS	B11	High	Input
$\overline{\text{TRST}}$	C10	Low	Input
$\overline{\text{TS}}$	J13	Low	I/O
TSIZ[0-2]	A13, D10, B12	High	Output
TT[0-4]	B13, A15, B16, C14, C15	High	I/O
WT	D2	Low	Output
VDD (2)	F6, F8, F9, F11, G7, G10, H6, H8, H9, H11, J6, J8, J9, J11, K7, K10, L6, L8, L9, L11	—	—
VOLTDETGND (3)	F3	Low	Output

NOTES:

1. These are test signals for factory use only and must be pulled up to OVdd for normal machine operation.
2. OVdd inputs supply power to the I/O drivers and Vdd inputs supply power to the processor core.
3. Internally tied to GND in the BGA package to indicate to the power supply that a low-voltage processor is present.

RECOMMENDED OPERATING CONDITIONS

Characteristic	Symbol	Value	Unit
Core supply voltage	Vdd	2.5 to 2.7	V
PLL supply voltage	AVdd	2.5 to 2.7	V
60x bus supply voltage	OVdd	3.135 to 3.465	V
Input supply	Vin	GND to OVdd	V
Ambient temperature (Mil)	TA	-55 to +125	°C
Ambient temperature (Ind)	TA	-40 to +85	°C

NOTE:

These are the recommended and tested operating conditions. Proper device operation outside of these conditions is not guaranteed

ABSOLUTE MAXIMUM RATINGS

Characteristic	Symbol	Value	Unit
Core supply voltage	Vdd	-0.3 to 2.75	V
PLL supply voltage	AVdd	-0.3 to 2.75	V
60x bus supply voltage	OVdd	-0.3 to 3.6	V
Input supply	Vin	-0.3 to 3.6	V
Storage temperature range	Tstg	-55 to 150	°C

NOTES:

1. Functional and tested operating conditions are given in Operating Conditions table. Absolute maximum ratings are stress ratings only, and functional operation at the maximums is not guaranteed. Stresses beyond those listed may affect device reliability or cause permanent damage to the device.
2. Caution: Vin must not exceed OVdd by more than 0.3V at any time including during power-on reset.
3. Caution: OVdd must not exceed Vdd/AVdd by more than 1.2 V at any time including during power-on reset.
4. Caution: Vdd/AVdd must not exceed OVdd by more than 0.4 V at any time including during power-on reset.
5. L2 AVdd is internally tied to AVdd. L2 OVdd is internally tied to OVdd.



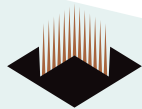
POWER CONSUMPTION

Vdd=AVdd=2.5±0.1V Vdc, OVdd=3.3 ±5% Vdc, GND=0 Vdc, 0≤Tj<105°C

		Processor (CPU) Frequency/L2 Frequency 200 MHz/133MHz	Unit	Notes
Full-on Mode	Typical	6.7	W	1,3
	Maximum	8.0	W	1, 2
Doze Mode	Maximum	2.75	W	1, 2
Nap Mode	Maximum	500	mW	1, 2
Sleep Mode	Maximum	350	mW	1, 2
Sleep Mode-PLL and DLL Disabled	Maximum	50	mW	1, 2

NOTES:

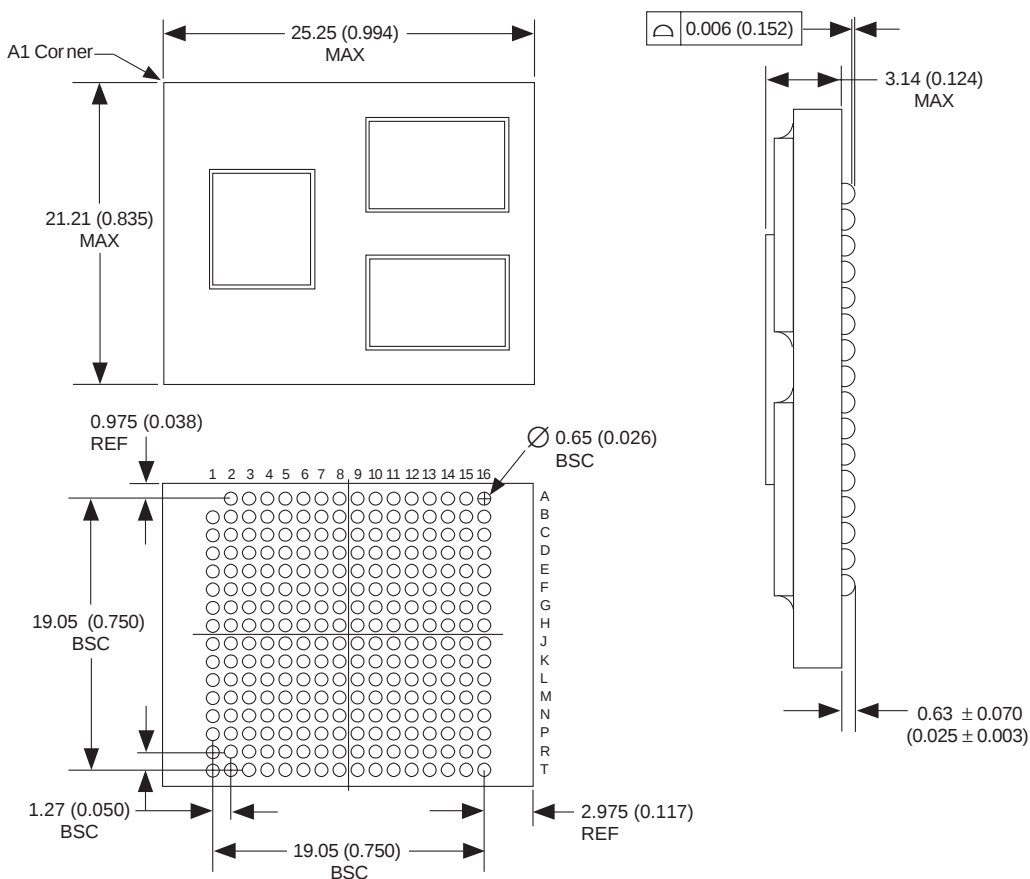
1. These values apply for all valid 60x bus and L2 bus ratios. The values do not include OVdd. OVdd power is system dependent, but is typically <10% of Vdd power. Worst case power consumption, for AVdd=35 mw.
2. Maximum power is measured at Vdd=2.625 V using a worst-case instruction mix.
3. Typical power is an average value measured at Vdd=AVdd=2.5V, OVdd=3.3V in a system, executing typical applications and benchmark sequences.



PACKAGE DESCRIPTION

Package Outline	21x25mm
Interconnects	255 (16x16 ball array less one)
Pitch	1.27mm
Maximum module height	3.90mm
Ball diameter	0.65mm

PACKAGE DIMENSIONS 255 BALL GRID ARRAY



NOTES:

1. Dimensions in millimeters and paranthetically in inches.
2. A1 corner is designated with a ball missing the array.



ORDERING INFORMATION

WED 3 C 750A 8M 200 X X

DEVICE GRADE:

I = Industrial

-40°C to +85°C

M = Military Screened

-55°C to +125°C

PACKAGE TYPE:

B = 255 Ceramic Ball Grid Array

C = 255 Ceramic Column Grid Array*

CORE FREQUENCY (MHz)

L2 CACHE DENSITY:

8Mbits = 128K x 72 SSRAM

PowerPC™:

Type 750A

C = MCM-C

3 = PowerPC™

WHITE ELECTRONIC DESIGNS CORP.

** Advanced Package, contact factory for availability.*

PowerPC™ is a trademark of International Business Machine Corp.